



PTO/SB/08A (08-03)

INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)			Complete if Known		
			Application Number	10/666,034	
			Filing Date	September 18, 2003	
			First Named Inventor	Kocon, Christopher Boguslaw	
			Art Unit	2814	
Sheet	1	of	12	Examiner Name	Long Pham
				Attorney Docket Number	018865-009010US

U.S. PATENT DOCUMENTS+					
Examiner Initials	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number Kind Code ² (if known)			
LP	1	US-3,404,295	10-01-1968	Warner et al.	
	2	US-3,412,297	11-19-1968	Amlinger	
	3	US-3,497,777	02-24-1970	Teszner et al.	
	4	US-3,564,356	02-16-1971	Wilson	
	5	US-3,660,697	05-02-1972	Berglund et al.	
	6	US-4,003,072	01-11-1977	Matsushita et al.	
	7	US-4,300,150	11-10-1981	Colak	
	8	US-4,326,332	04-27-1982	Kenney et al.	
	9	US-4,337,474	06-29-1982	Yukimoto	
	10	US-4,345,265	08-17-1982	Blanchard	
	11	US-4,445,202	04-24-1984	Geotze et al.	
	12	US-4,579,621	04-01-1986	Hine	
	13	US-4,636,281	01-13-1987	Buiguez et al.	
	14	US-4,638,344	01-20-1987	Cardwell, Jr.	
	15	US-4,639,761	01-27-1987	Singer et al.	
	16	US-4,698,653	10-06-1987	Cardwell, Jr.	
	17	US-4,716,126	12-29-1987	Cogan	
	18	US-4,746,630	05-24-1988	Hui et al.	
	19	US-4,754,310	06-28-1988	Coe	
	20	US-4,774,556	09-27-1988	Fujii et al.	
	21	US-4,801,986	01-31-1989	Chang et al.	
	22	US-4,821,095	04-11-1989	Temple	
	23	US-4,823,176	04-18-1989	Baliga et al.	
	24	US-4,853,345	08-01-1989	Himelick	
	25	US-4,868,624	09-19-1989	Grung et al.	
	26	US-4,893,160	01-09-1990	Blanchard	
	27	US-4,914,058	04-03-1990	Blanchard	
	28	US-4,941,026	07-10-1990	Temple	
	29	US-4,967,245	10-30-1990	Cogan et al.	
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	31	US-4,974,059	11-27-1990	Kinzer	
	32	US-4,990,463	02-05-1991	Mori	
	33	US-4,992,390	02-12-1991	Hsueh-Rong Chang	
	34	US-5,027,180	06-25-1991	Nishizawa et al.	
	35	US-5,034,785	07-23-1991	Blanchard	
	36	US-5,071,782	12-10-1991	Mori	
	37	US-5,072,266	12-10-1991	Buluccea	
	38	US-5,079,608	01-07-1992	Wodarczyk et al.	
	39	US-5,105,243	04-14-1992	Nakagawa et al.	
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	41	US-5,142,640	08-25-1992	Iwanatsu	

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Sheet	2	of	12	Attorney Docket Number	018865-009010US

U.S. PATENT DOCUMENTS+					
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LP	42	US-5,164,325	11-17-1992	Cogan et al.	
	43	US-5,164,802	11-17-1992	Jones et al.	
	44	US-5,216,275	06-01-1993	Chen	
	45	US-5,219,777	06-15-1993	Kang	
	46	US-5,219,793	06-15-1993	Cooper et al.	
	47	US-5,233,215	08-03-1993	Baliga	
	48	US-5,262,336	11-16-1993	Pike, Jr. et al.	
	49	US-5,268,311	12-07-1993	Euen et al.	
	50	US-5,275,965	01-04-1994	Manning	
	51	US-5,294,824	03-15-1994	Okada	
	52	US-5,298,761	03-29-1994	Cogan et al.	
	53	US-5,300,447	04-05-1994	Anderson	
	54	US-5,326,711	07-05-1994	Malhi	
	55	US-5,350,937	09-27-1994	Yamazaki et al.	
	56	US-5,365,102	11-15-1994	Mehrotra et al.	
	57	US-5,366,914	11-22-1994	Takahashi et al.	
	58	US-5,389,815	02-14-1995	Takahashi	
	59	US-5,405,794	04-11-1995	Kim	
	60	US-5,418,376	05-23-1995	Muraoka et al.	
	61	US-5,424,231	06-13-1995	Yang	
	62	US-5,429,977	07-04-1995	Lu et al.	
	63	US-5,430,311	07-04-1995	Murakami et al.	
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	65	US-5,436,189	07-25-1995	Beasom	
	66	US-5,438,215	08-01-1995	Tihanyi	
	67	US-5,442,214	08-15-1995	Yang	
	68	US-5,454,435	07-18-1995	Baliga	
	69	US-5,473,176	12-05-1995	Kakumoto	
	70	US-5,473,180	12-05-1995	Ludikhuize	
	71	US-5,474,943	12-12-1995	Hshieh et al.	
	72	US-5,519,245	05-21-1996	Tokura et al.	
	73	US-5,541,425	07-30-1996	Nishihara	
74	US-5,554,862	09-10-1996	Omura et al.		
75	US-5,567,634	10-22-1996	Hebert et al.		
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77	US-5,572,048	11-05-1996	Sugawara		
78	US-5,576,245	11-19-1996	Cogan et al.		
79	US-5,578,851	11-26-1996	Hshieh et al.		
80	US-5,581,100	12-03-1996	Ajit		
81	US-5,583,065	12-10-1996	Miwa		
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		Number Kind Code ² (if known)			
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	84	US-5,597,765	01-28-1997	Yilmaz et al.	
	85	US-5,605,852	02-25-1997	Bencuya	
	86	US-5,616,945	04-01-1997	Williams	
	87	US-5,623,152	04-22-1997	Majumdar et al.	
	88	US-5,629,543	05-13-1997	Hshieh et al.	
	89	US-5,637,898	06-10-1997	Bailga	
	90	US-5,639,676	06-17-1997	Hshieh et al.	
	91	US-5,640,034	07-17-1997	Satwinder Malhi	
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	93	US-5,656,843	08-12-1997	Goodyear et al.	
	94	US-5,665,619	09-09-1997	Kwan et al.	
	95	US-5,670,803	09-23-1997	Beilstein, Jr. et al.	
	96	US-5,689,128	11-18-1997	Hshieh et al.	
	97	US-5,693,569	12-02-1997	Ueno	
	98	US-5,705,409	01-06-1998	Witek	
	99	US-5,710,072	01-20-1998	Krautschneider et al.	
	100	US-5,714,781	02-03-1998	Yamamoto et al.	
	101	US-5,719,409	02-17-1998	Singh et al.	
	102	US-5,744,372	04-28-1998	Bulucea	
	103	US-5,770,878	06-23-1998	Beasom	
	104	US-5,776,813	07-07-1998	Huang et al.	
	105	US-5,780,343	07-14-1998	Bashir	
106	US-5,801,417	09-01-1998	Tsang et al.		
107	US-5,814,858	09-29-1998	Williams		
108	US-5,877,528	03-02-1999	So		
109	US-5,879,971	03-09-1999	Witek		
110	US-5,879,994	03-09-1999	Kwan et al.		
111	US-5,895,951	04-20-1999	So et al.		
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113	US-5,897,343	04-27-1999	Mathew et al.		
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115	US-5,900,663	05-04-1999	Johnson et al.		
116	US-5,906,680	05-25-1999	Meyerson		
117	US-5,917,216	06-29-1999	Floyd et al.		
118	US-5,929,481	07-27-1999	Hsieh et al.		
119	US-5,943,581	08-24-1999	Lu et al.		
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		Number Kind Code ² (if known)			
LP	124	US-5,972,741	10-26-1999	Kubo et al.	
	125	US-5,973,360	10-26-1999	Tihanyi	
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	131	US-6,005,271	12-21-1999	Hsieh	
	132	US-6,008,097	12-28-1999	Yoon et al.	
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	134	US-6,015,727	01-18-2000	Wanlass	
	135	US-6,020,250	02-01-2000	Kenny et al.	
	136	US-6,034,415	05-07-2000	Johnson et al.	
	137	US-6,037,202	03-14-2000	Witek	
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	139	US-6,037,632	03-14-2000	Omura et al.	
140	US-6,040,600	03-21-2000	Uenishi et al.		
141	US-6,048,772	04-11-2000	D'Anna		
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143	US-6,057,558	05-02-2000	Yamamoto et al.		
144	US-6,063,678	05-16-2000	D'Anna		
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146	US-6,066,878	05-23-2000	Neilson		
147	US-6,069,043	05-30-2000	Floyd et al.		
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151	US-6,087,232	07-11-2000	Kim et al.		
152	US-6,096,608	08-01-2000	Williams		
153	US-6,097,063	08-01-2000	Fujihira		
154	US-6,103,578	08-15-2000	Uenishi et al.		
155	US-6,104,054	08-15-2000	Corsi et al.		
156	US-6,110,799	08-29-2000	Huang		
157	US-6,114,727	09-05-2000	Ogura et al.		
158	US-6,137,152	10-24-2000	Wu		
159	US-6,150,697	11-21-2000	Teshigahara et al.		
160	US-6,156,606	12-05-2000	Michaelis		
161	US-6,156,611	12-05-2000	Lan et al.		
162	US-5,168,973	12-08-1992	Asayama et al.		
163	US-6,163,052	12-19-2000	Liu et al.		
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LP	165	US-6,168,983	01-02-2001	Rumennik et al.	
	166	US-6,168,996	01-02-2001	Numazawa et al.	
	167	US-6,171,935	01-09-2001	Nance et al.	
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	172	US-6,188,104	02-13-2001	Choi et al.	
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	174	US-6,190,978	02-20-2001	D'Anna	
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	183	US-6,228,727	05-08-2001	Lim et al.	
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193	US-6,281,547	08-28-2001	So et al.		
194	US-6,285,060	09-04-2001	Korec et al.		
195	US-6,291,298	09-18-2001	Williams et al.		
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197	US-6,294,818	09-25-2001	Fujihira		
198	US-6,297,534	10-02-2001	Kawaguchi et al.		
199	US-6,303,969	10-16-2001	Tan		
200	US-6,307,246	10-23-2001	Nitta et al.		
201	US-6,309,920	10-30-2001	Laska et al.		
202	US-6,313,482	11-06-2001	Baliga		
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LP	206	US-6,346,464	02-12-2002	Takeda et al	
	207	US-6,346,469	02-12-2002	Greer	
	208	US-6,351,018	02-26-2002	Sapp	
	209	US-6,353,252	03-05-2002	Yasuhara et al.	
	210	US-6,359,308	03-19-2002	Hijzen et al.	
	211	US-6,362,112	03-26-2002	Hamerski	
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	213	US-6,365,462	04-02-2002	Baliga	
	214	US-6,365,930	04-02-2002	Schillaci et al.	
	215	US-6,368,920	04-09-2002	Beasom	
	216	US-6,368,921	04-09-2002	Hijzen et al	
	217	US-6,376,314	04-23-2002	Jerred	
	218	US-6,376,878	04-23-2002	Kocon	
	219	US-6,376,890	04-23-2002	Tihanyi	
	220	US-6,384,456	05-07-2002	Tihanyi	
	221	US-6,388,286	05-14-2002	Baliga	
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	223	US-6,400,003	06-04-2002	Huang	
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	225	US-6,433,385	08-13-2002	Kocon et al.	
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	243	US-6,608,350	08-27-2003	Kinzer et al.	
	244	US-6,677,641	01-13-2004	Kocon	
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	246	US-2001/0028083 A1	10-11-2001	Onishi et al.	

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Substitute for form 1449A/PTO			Complete If Known		
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)			Application Number	10/666,034	
			Filing Date	September 18, 2003	
			First Named Inventor	Kocon, Christopher Boguslaw	
			Art Unit	2814	
			Examiner Name	Long Pham	
Sheet	7	of	12	Attorney Docket Number	018865-009010US

U.S. PATENT DOCUMENTS+					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number Kind Code ² (if known)			
LP ↓	247	US-2001/0032998 A1	10-25-2001	Iwamoto et al.	
	248	US-2001/0041400 A1	11-15-2001	Ren et al.	
	249	US-2001/0049167 A1	12-06-2001	Madson	
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	253	US-2002/0066924 A1	06-06-2002	Blanchard	
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	255	US-2003/0060013 A1	03-27-2003	Marchant	
	256	US-2003/0100933 A1	08-01-2002	Marchant	
	257	US-2003/0132450 A1	07-17-2003	Minato et al.	
	258	US-2003/0193067 A1	10-16-2003	Kim	

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		Country Code ³	Number ⁴	Kind Code ⁵ (if known)				
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LP	269	JP	56-058267	A	05-21-1981	Nippon Telegr & Teleph Corp.		<input checked="" type="checkbox"/>
	270	JP	62-069562		03-30-1987	Mitsubishi Electric Corp		<input checked="" type="checkbox"/>
	271	JP	63-186475		08-02-1988	Nissan Motor Co. LTD.		<input checked="" type="checkbox"/>
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	273	JP	64-022051		01-25-1989	Matsushita Electric Ind		<input checked="" type="checkbox"/>
	274	JP	2000-040822		02-08-2000	Fuji Electric Co. LTD.		<input checked="" type="checkbox"/>
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	276	JP	2000-156978	A	06-06-2000	Fuji Electric Co. LTD.		<input checked="" type="checkbox"/>
	277	JP	2000-277726	A	10-06-2000	Toshiba Corp.		<input checked="" type="checkbox"/>
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	284	JP	2001-144292	A	05-25-2001	Denso Corp.		<input checked="" type="checkbox"/>
	285	JP	2001-244461	A	09-07-2001	Toyota Central Res & Dev Lab INC.		<input checked="" type="checkbox"/>
	286	JP	2001-313391	A	12-20-2001	S. Takahiro et al.		<input checked="" type="checkbox"/>
	287	JP	2002-083976	A	03-22-2002	Naito et al.		<input checked="" type="checkbox"/>
	288	PCT	WO 00/33386	A2	06-08-2000	Koninklijke Philips Electronics		<input type="checkbox"/>
	289	PCT	WO 00/68997	A1	11-16-2000	C.P. Clare Corporation		<input type="checkbox"/>
	290	PCT	WO 00/68998	A1	11-16-2000	C.P. Clare Corporation		<input type="checkbox"/>
	291	PCT	WO 00/75965	A2	12-14-2000	General Semiconductor, Inc.		<input type="checkbox"/>
	292	PCT	WO 01/06550	A1	01-23-2001	Koninklijke Philips Electronics		<input type="checkbox"/>
	293	PCT	WO 01/06557	A1	01-25-2001	Koninklijke Philips Electronics		<input type="checkbox"/>
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	295	PCT	WO 01/59847	A2	08-16-2001	Koninklijke Philips Electronics		<input type="checkbox"/>
	296	PCT	WO 01/71815		09-27-2001	Koninklijke Philips Electronics		<input type="checkbox"/>
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60436135 v1

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				Application Number	10/666,034
				Filing Date	September 18, 2003
				First Named Inventor	Kocon, Christopher Boguslaw
				Art Unit	2814
Examiner Name	Long Pham				
Sheet	9	of	12	Attorney Docket Number	018865-009010US

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		Country Code ³	Number ⁴	Kind Code ⁵ (if known)				
LP ↓	298	PCT	WO 01/95398	A1	12-13-2001	General Semiconductor, Inc.		<input type="checkbox"/>
	299	PCT	WO 02/01644	A2	01-03-2002	Silicon Wireless Corporation		<input type="checkbox"/>
	300	PCT	WO 02/047171	A1	06-13-2002	International Rectifier Corporation		<input type="checkbox"/>
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Examiner Initials *	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
LH	301	BAI et al., "Novel automated optimization of power MOSFET for 12V input, high-frequency DC-DC converter," <i>International Symposium on Power Semiconductors and ICs, Technical Digest</i> , (2003), pp. 366-369.	
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LP ↓	333	Technical Literature from Quester Technology, Model APT-4300 300mm Atmospheric TEOS/Ozone CVD System, (unknown date), 3 pages total.	
	334	Technical Literature from Quester Technology, Model APT-6000 Atmospheric TEOS-Ozone CVD System, (unknown date), 2 pages total.	
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